

[TABLE 1]

ITEMS		FIRST AMORPHOUS SEMICONDUCTOR FILM	SECOND AMORPHOUS SEMICONDUCTOR FILM
SiH ₄ FLOW AMOUNT	[sccm]	50~95	100
GeH ₄ (H ₂ -BASE 10%) FLOW AMOUNT	[sccm]	50~5	0
RF POWER	[W/cm ²]	0.35	←
PULSE FREQUENCY	[KHz]	10	←
DUTY	[%]	30	←
PRESSURE	[Pa]	33.25	←
SUBSTRATE TEMPERATURE (T _{sub})	[°C]	300	←
ELECTRODE GAP (GAP)	[mm]	35	←

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